

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
20V	380mΩ@4.5V	0.75A
	450mΩ@2.5V	
-20V	520mΩ@-4.5V	-0.66A
	700mΩ@-2.5V	

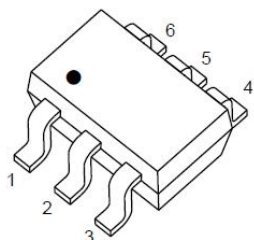
Feature

- Trench Technology
- Supper high density cell design for extremely low $R_{ds(on)}$
- Exceptional ON resistance and maximum DC current capability
- ESD protected Gate HBM 2KV

Application

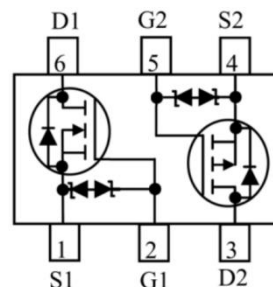
- Driver: Relays, Solenoids, Lamps, Hammers
- Power supply converters circuit
- Load/Power Switching for potable device

Package

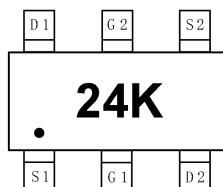


SOT-363

Circuit diagram



Marking



24K =Device Code

**Absolute maximum ratings (Ta=25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit
Power Dissipation	P_D	0.15	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	833	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~ +150	°C

Maximum Ratings - N-Channel Q1(Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current	I_D	0.75	A

Maximum Ratings - P-Channel Q2(Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	±10	V
Continuous Drain Current	I_D	-0.66	A

Electrical characteristics - N-Channel Q1 (T_A=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	20			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 16V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$			± 10	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.35	0.65	1	V
Drain-source on-resistance	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 0.5A$		0.25	0.38	Ω
		$V_{GS} = 2.5V, I_D = 0.2A$		0.35	0.45	
		$V_{GS} = 1.8V, I_D = 0.1A$		0.4		
Dynamic characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 16V, V_{GS} = 0V, f = 1MHz$		79	120	pF
Output Capacitance	C_{oss}			13	20	
Reverse Transfer Capacitance	C_{rss}			9	15	
Switching Characteristics						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = 4.5V, V_{DS} = 10V, I_D = 500mA, R_{GEN} = 10\Omega$		6.7		ns
Turn-on rise time	t_r			4.8		



Turn-off delay time	$t_{d(off)}$		17.3		
Turn-off fall time	t_f		7.4		
Source-Drain Diode characteristics					
Body Diode Voltage	V_{SD}	$I_S=0.5A, V_{GS}=0V$	0.7	1.3	V

Electrical characteristics - P-Channel Q2 ($T_A=25^\circ C$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -16V, V_{GS} = 0V$			-1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$			± 10	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.35		-1.0	V
Drain-source on-resistance ¹⁾	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -0.5A$		0.43	0.52	Ω
		$V_{GS} = -2.5V, I_D = -0.2A$		0.62	0.7	
		$V_{GS} = -1.8V, I_D = -0.1A$		0.95		
Dynamic characteristics ²⁾						
Input Capacitance	C_{iss}	$V_{DS} = -16V, V_{GS} = 0V, f = 1MHz$		113		pF
Output Capacitance	C_{oss}			15		
Reverse Transfer Capacitance	C_{rss}			9		
Turn-on delay time	$t_{d(on)}$	$V_{DS} = -10V, I_D = -200mA, V_{GS} = -4.5V, R_G = 10\Omega$		9		ns
Turn-on rise time	t_r			5.7		
Turn-off delay time	$t_{d(off)}$			32.6		
Turn-off fall time	t_f			20.3		
Source-Drain Diode characteristics						
Diode Forward voltage	V_{SD}	$V_{GS} = 0V, I_S = -0.5A$			-1.2	V

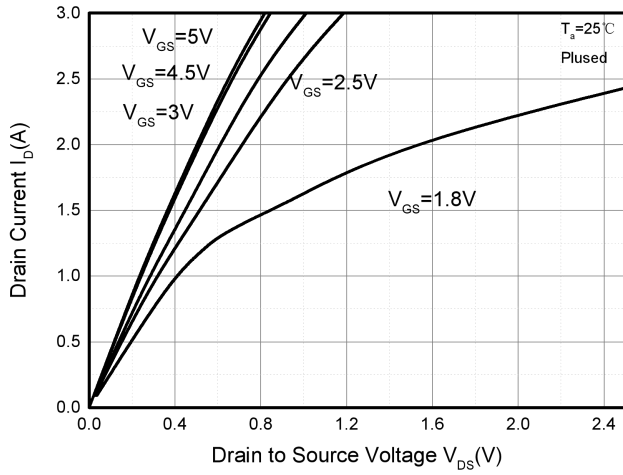
Notes:

1. Pulse Test: Pulse Width $< 300\mu s$, Duty Cycle $\leq 2\%$.
2. Guaranteed by design, not subject to production testing.

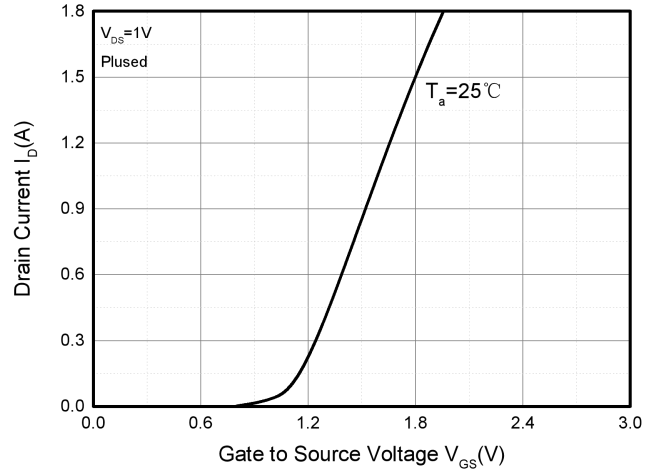


Typical Characteristics - N-Channel Q1

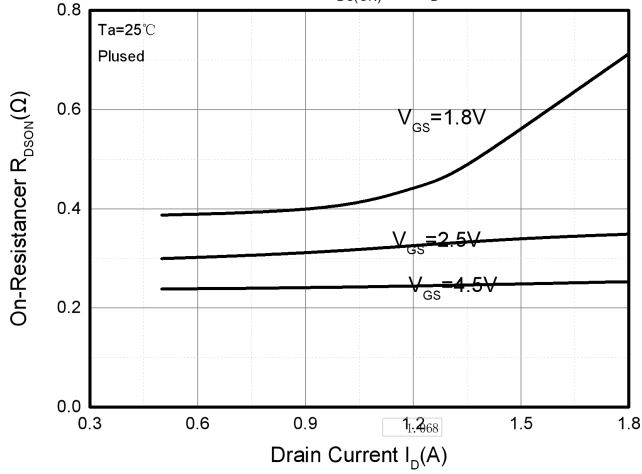
Output Characteristics



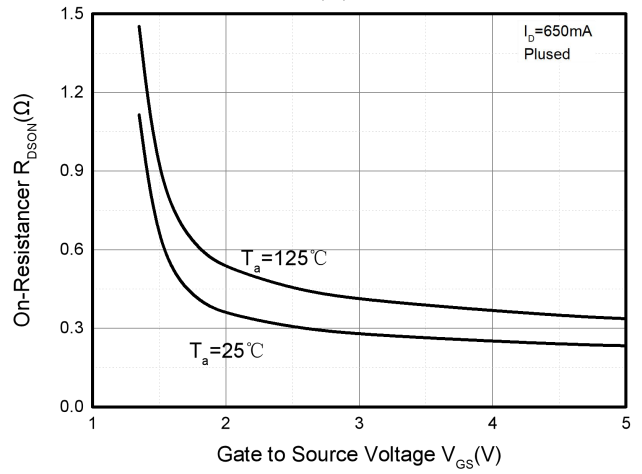
Transfer Characteristics



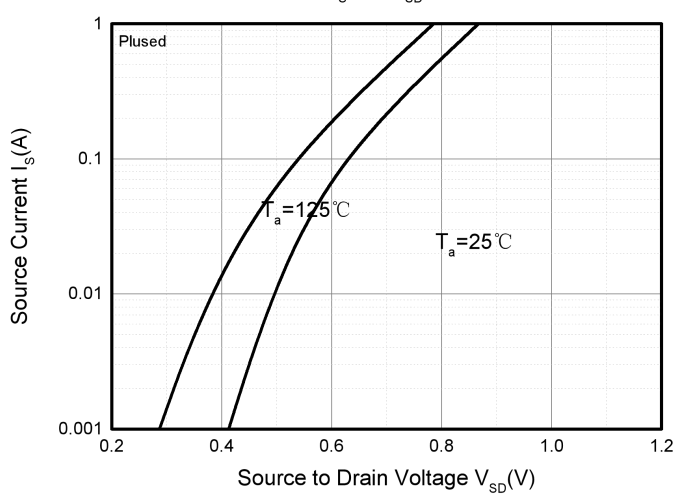
$R_{DS(ON)} - I_D$



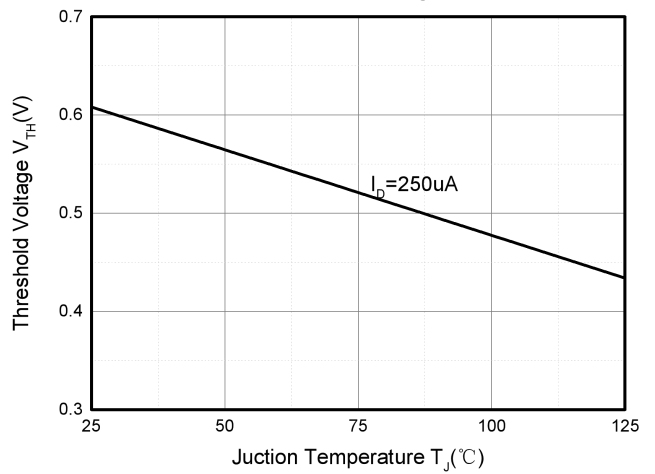
$R_{DS(ON)} - V_{GS}$



$I_S - V_{SD}$

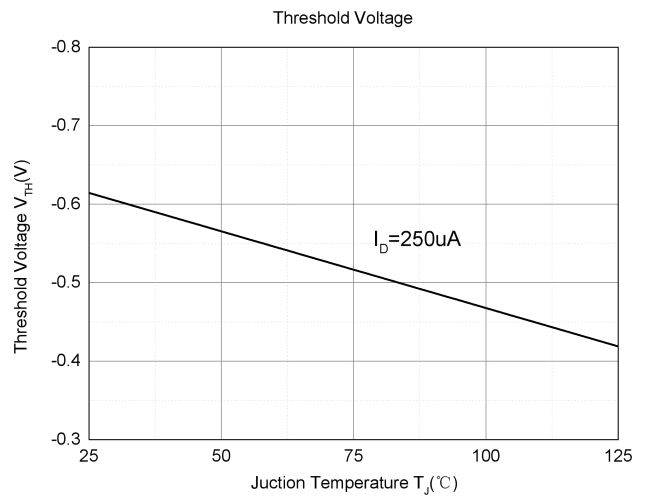
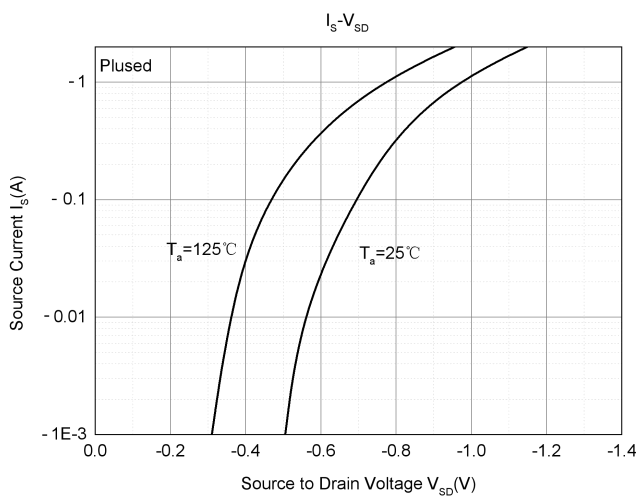
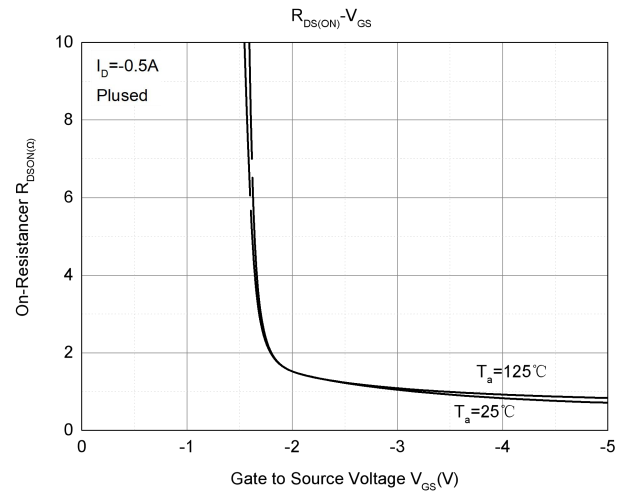
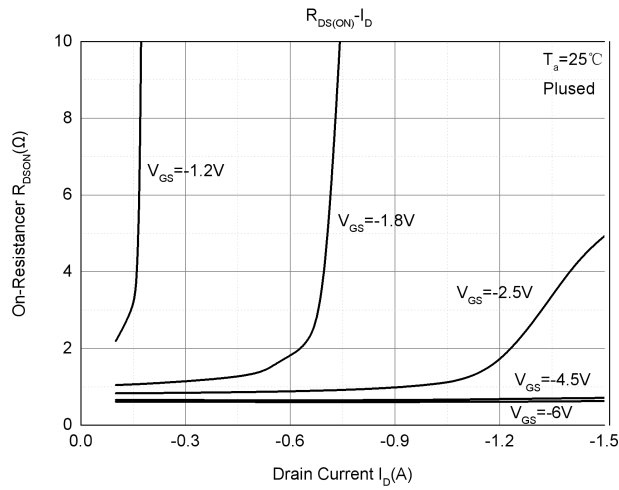
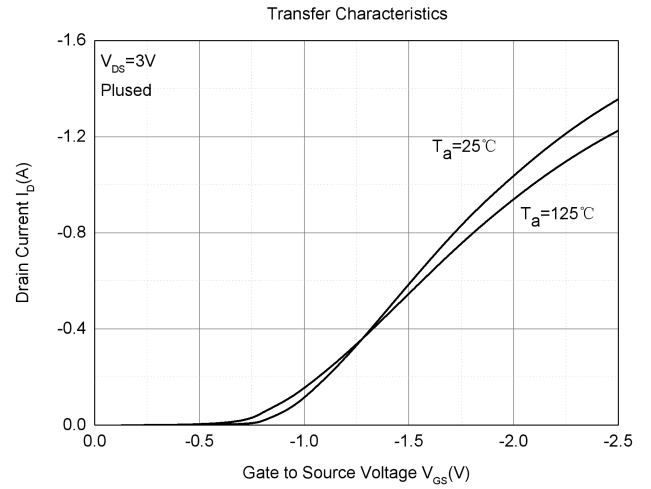
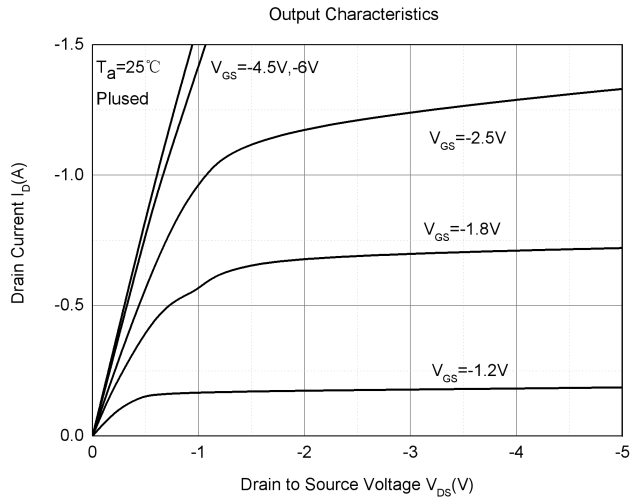


Threshold Voltage



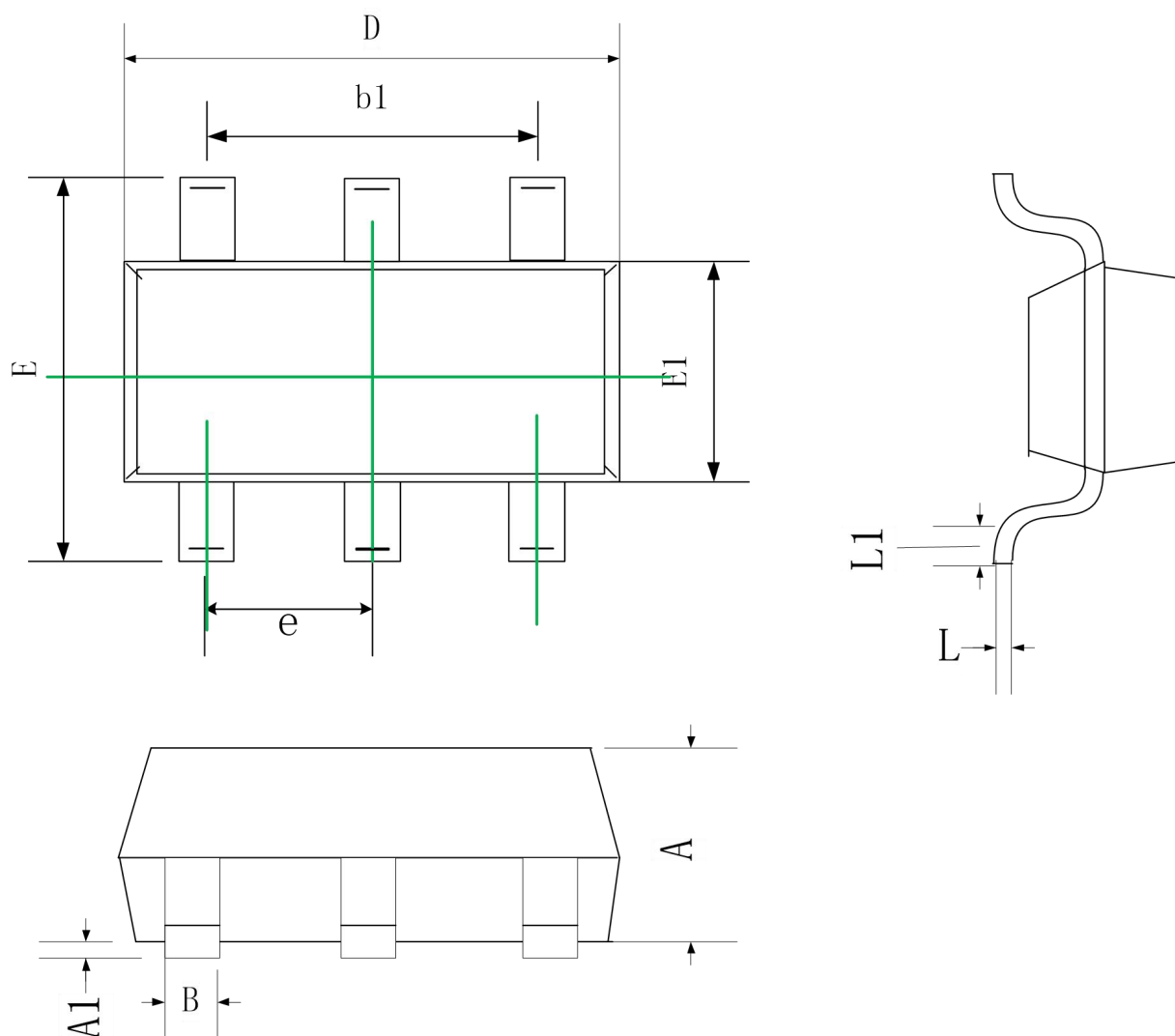


Typical Characteristics - P-Channel Q2





SOT-363 Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.00
A1	0.00	0.10
B	0.10	0.30
b1	1.30	
D	1.80	2.20
E	2.00	2.20
E1	1.15	1.35
e	0.65 TYP.	
L	0.10	0.25
L1	0.15	0.4

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